

L Number	Hits	Search Text	DB	Time stamp
1	31	integrated near2 heater and transistor and semiconductor and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:37
2	0	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and smiconductor with wall	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:37
3	1	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor near2 wall	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:38
4	6	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor with wall	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:57
5	0	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor with wall near2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:41
6	2	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor with wall with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:43
7	27	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 11:43
8	6	((integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor with wall) and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 12:02
9	6	((((integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor with wall) and gate adj electrode) and (fluid or liquid)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 12:12
10	1	(((((integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and semiconductor with wall) and gate adj electrode) and (fluid or liquid))) and dielectric with window	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 12:12
11	3	(integrated near2 heater and transistor and semiconductor and 257/\$.ccls.) and dielectric with window	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/22 12:12